





N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance: R_{DS(ON)}
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

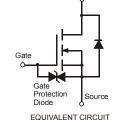
Case: SOT323

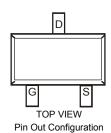
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42
 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

Drain









Ordering Information (Note 4)

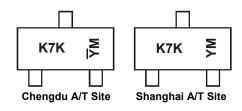
Part Number	Case	Packaging
DMN601WK-7	SOT323	3000/Tape & Reel

SOT323

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



K7K = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) $\overline{\gamma}_M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or $\overline{\gamma}$ = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	201	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		Α		В	(2	D		Е		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Charac	teristic	Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current (Note 5) Continuous Pulsed (Note 6)		le le	300 800	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	200	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-65 to +150	°C

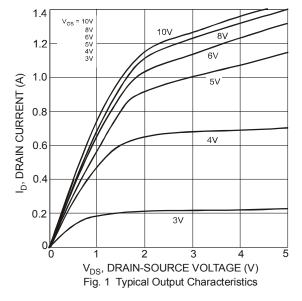
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60		_	V	$V_{GS} = 0V, I_{D} = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_		1.0	μA	V _{DS} = 60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_		±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	1.0	1.6	2.5	V	$V_{DS} = 10V, I_D = 1mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$	
Static Drain-Source On-Resistance		_		3.0		V _{GS} = 4.5V, I _D = 0.2A	
Forward Transfer Admittance	Y _{fs}	80		_	ms	$V_{DS} = 10V, I_D = 0.2A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_		50	pF		
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	_		5.0	pF		

Notes:

- 5. Device mounted on FR-4 PCB.
- 6. Pulse width ≤10μS, Duty Cycle ≤1%.
 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.





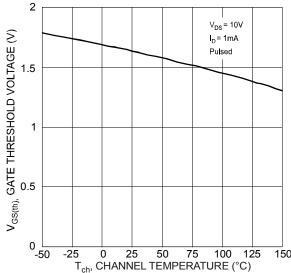
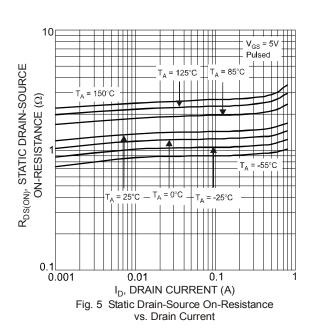
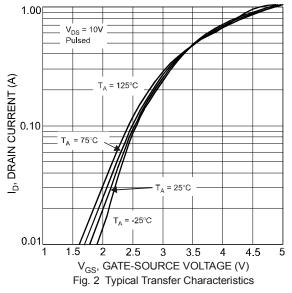


Fig. 3 Gate Threshold Voltage vs. Channel Temperature





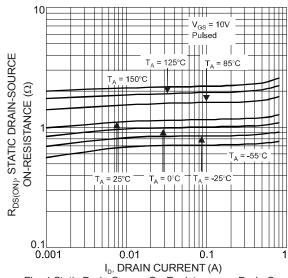


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

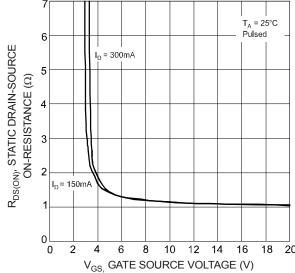
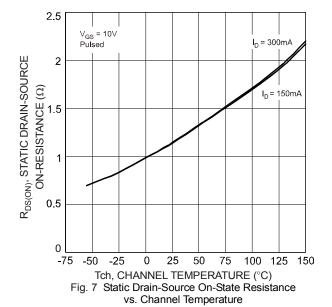
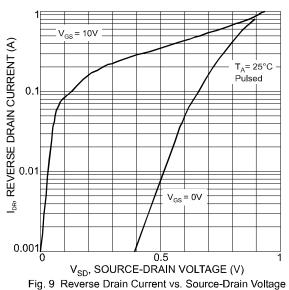


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage







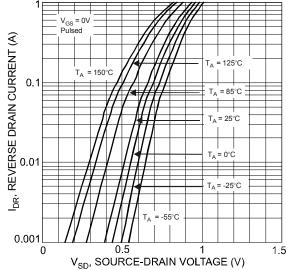


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

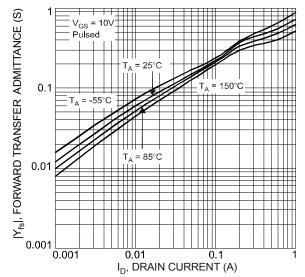
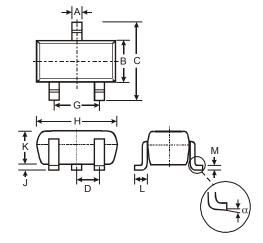


Fig.10 Forward Transfer Admittance vs. Drain Current

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

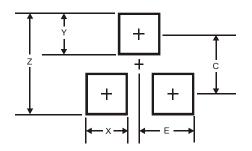


SOT323							
Dim	Min	Max	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D	-	-	0.65				
G	1.20	1.40	1.30				
Н	1.80	2.20	2.15				
J	0.0	0.10	0.05				
K	0.90	1.00	1.00				
L	0.25	0.40	0.30				
M	0.10	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

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